

80 V, single N-channel Trench MOSFET 18 December 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quid	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	80	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	-	2.8	А
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 1.9 A; T _j = 25 °C		-	175	230	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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80 V, single N-channel Trench MOSFET

5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G (T
4	S	source		
5	D	drain	Transparent top view DFN2020MD-6 (SOT1220)	
6	D	drain		S 017aaa255
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
PMPB215ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes	
Type number	Marking code
PMPB215ENEA	2B

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	80	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{amb} = 25 °C; t ≤ 5 s	[1]	-	2.8	А
		V_{GS} = 10 V; T_{amb} = 25 °C	[1]	-	1.9	А
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.2	А
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	7.6	А

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PMPB215ENEA

80 V, single N-channel Trench MOSFET

Symbol	Parameter	Conditions		Min	Мах	Unit
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I _D = 0.27 A; DUT in avalanche (unclamped)		-	11.3	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.6	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.3	W
		T _{sp} = 25 °C		-	15.6	W
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	diode	·				,
I _S	source current	T _{amb} = 25 °C	[1]	-	0.8	А
ESD maximun	n rating	1				,
V _{ESD}	electrostatic discharge voltage	HBM	[2]	-	2000	V

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Measured between all pins.

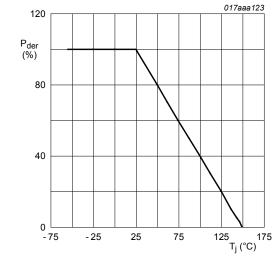


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

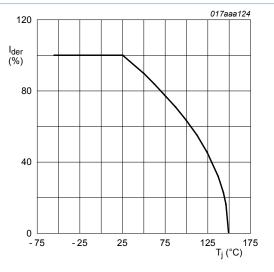
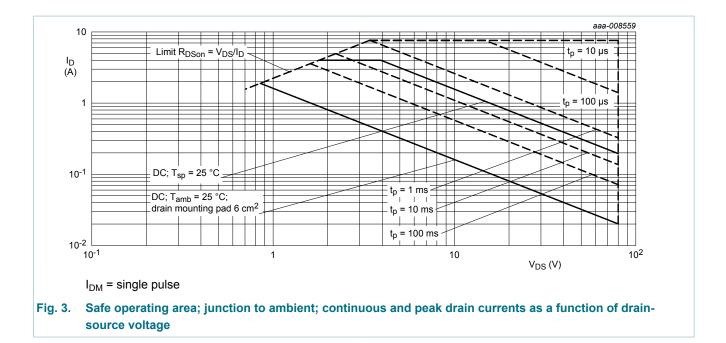


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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80 V, single N-channel Trench MOSFET



9. Thermal characteristics

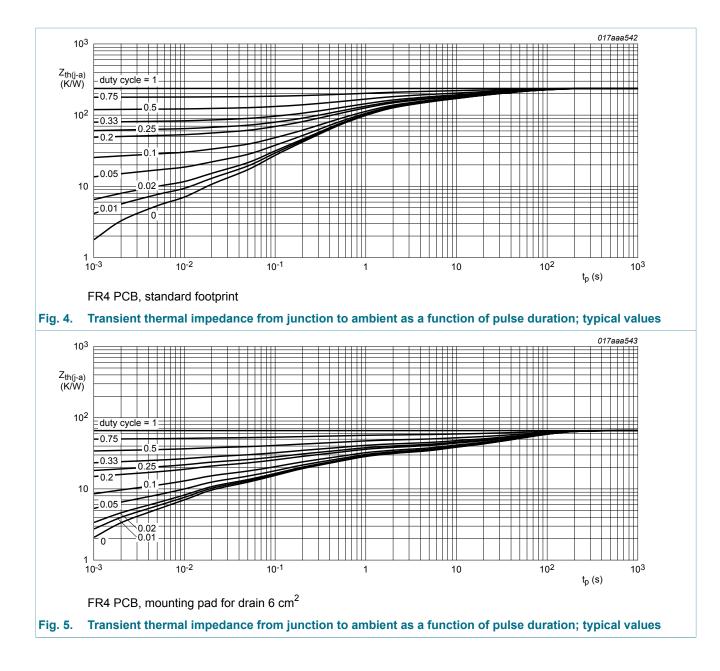
Table 6. The	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
ui(j-α)	thermal resistance	-	[1]	-	245	282	K/W
	from junction to ambient		[2]	-	68	78	K/W
		in free air; t ≤ 5 s	[2]	-	33	38	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	4	8	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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80 V, single N-channel Trench MOSFET

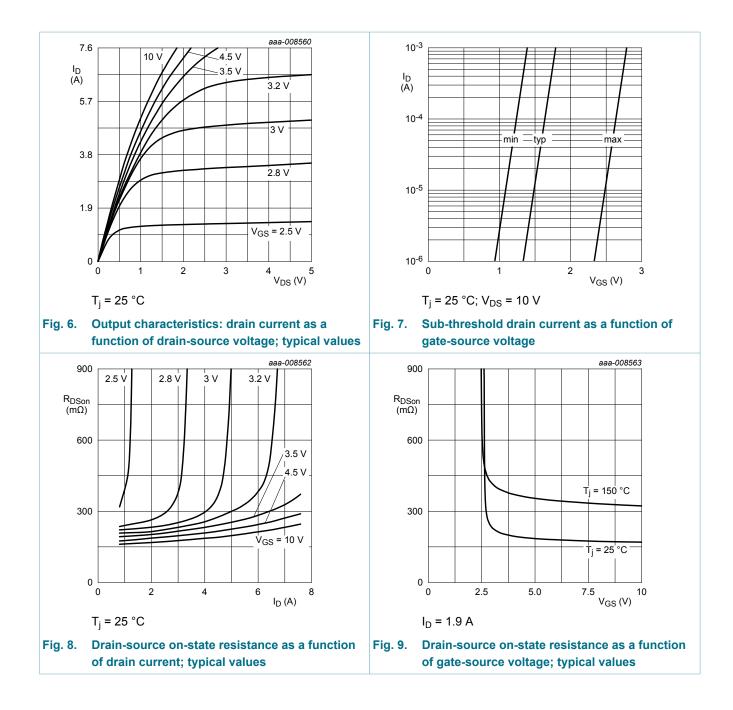


80 V, single N-channel Trench MOSFET

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	80	-	-	V
V _{GSth}	gate-source threshold voltage	I_D = 250 µA; V_{DS} = V_{GS} ; T_j = 25 °C	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{DS} = 80 V; V_{GS} = 0 V; T_j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	15	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-15	μA
		V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
R _{DSon} drain-source on-s resistance	drain-source on-state	V_{GS} = 10 V; I _D = 1.9 A; T _j = 25 °C	-	175	230	mΩ
	resistance	V_{GS} = 10 V; I _D = 1.9 A; T _j = 150 °C	-	340	445	mΩ
		V _{GS} = 4.5 V; I _D = 1.8 A; T _j = 25 °C	-	195	275	mΩ
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 1.9 A; T _j = 25 °C	-	7	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1	-	Ω
Dynamic ch	aracteristics		I			
Q _{G(tot)}	total gate charge	V_{DS} = 40 V; I _D = 1.9 A; V _{GS} = 10 V;	-	4.8	7.2	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.6	-	nC
Q _{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V_{DS} = 40 V; f = 1 MHz; V_{GS} = 0 V;	-	215	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	25	-	pF
C _{rss}	reverse transfer capacitance		-	15	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; I _D = 1.9 A; V _{GS} = 10 V;	-	3.5	-	ns
t _r	rise time	R _{G(ext)} = 6 Ω; T _j = 25 °C	-	2	-	ns
t _{d(off)}	turn-off delay time		-	9.5	-	ns
t _f	fall time		-	3	-	ns
Source-drai	n diode		I	- (
V _{SD}	source-drain voltage	I _S = 0.8 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

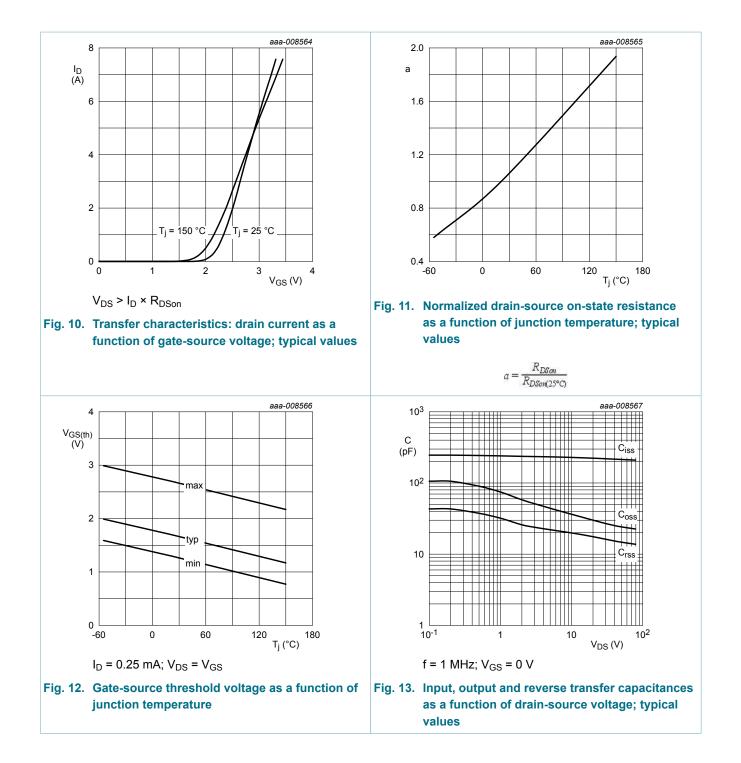
80 V, single N-channel Trench MOSFET



Product data sheet

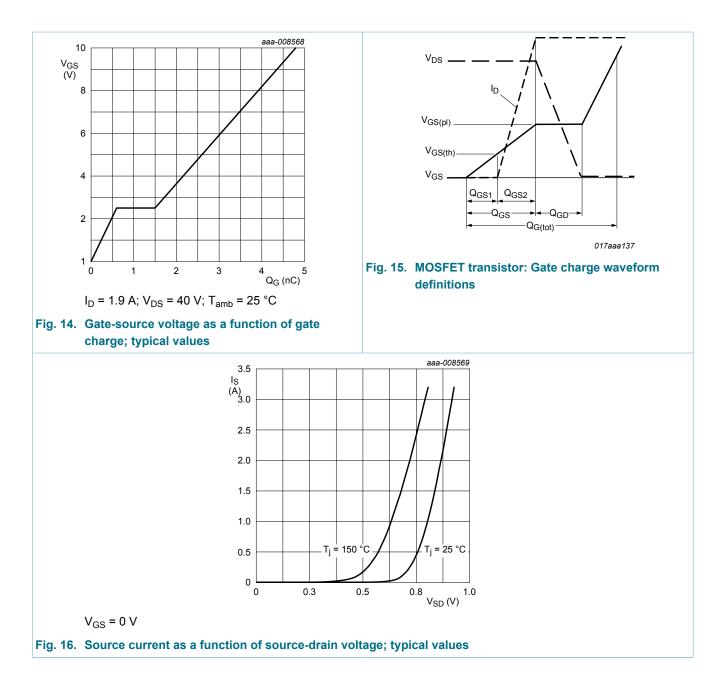
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80 V, single N-channel Trench MOSFET



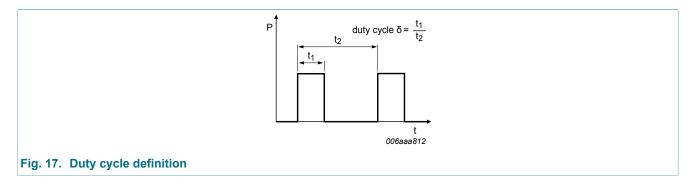
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80 V, single N-channel Trench MOSFET



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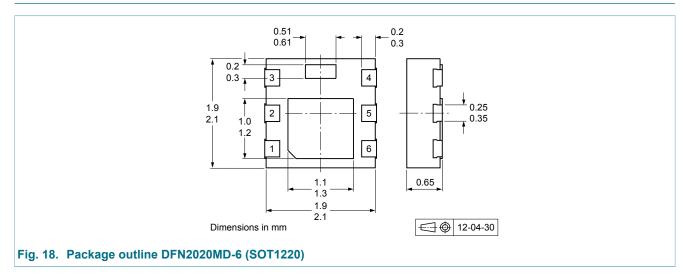
11. Test information



11.1 Quality information

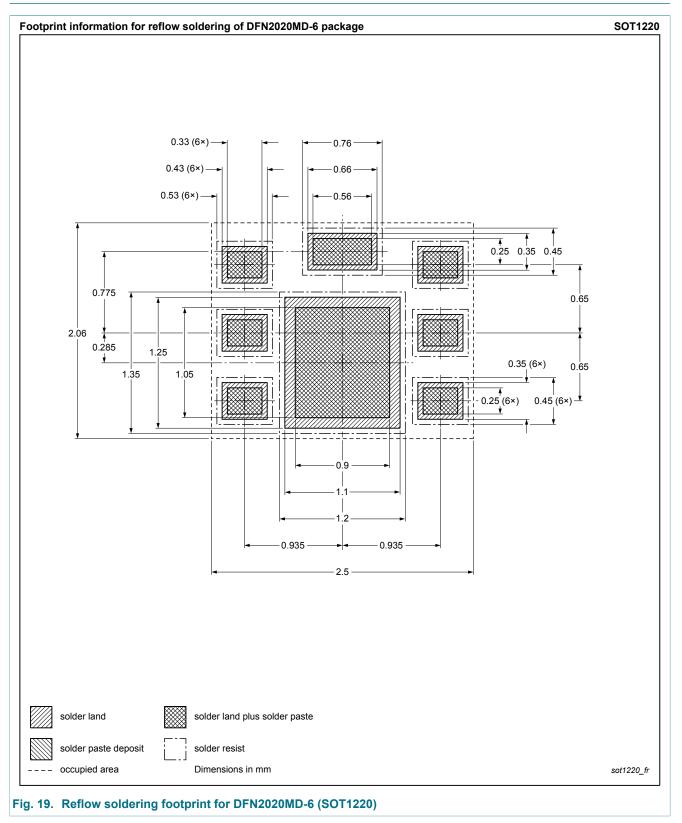
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



80 V, single N-channel Trench MOSFET

13. Soldering



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80 V, single N-channel Trench MOSFET

14. Revision history

Table 8. Revision hi	story			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB215ENEA v.2	20131218	Product data sheet	-	PMPB215ENEA v.1
Modifications:	Product status char	iged	·	
PMPB215ENEA v.1	20130219	Objective data sheet	-	-

80 V, single N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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80 V, single N-channel Trench MOSFET

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80 V, single N-channel Trench MOSFET

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	2
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	10
11.1	Quality information	10
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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